



2N5463, 2N5464, 2N5465 P-Channel JFET

Features

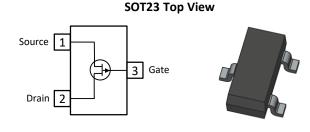
- InterFET P0032F Geometry
- Typical Noise: 2.7 nV/VHz
- Low Ciss: 3.2pF Typical
- RoHS Compliant
- SMT, TH, and Bare Die Package options.

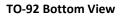
Applications

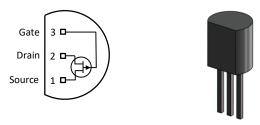
- Audio Amplifiers
- Small Signal Amplifiers
- General Purpose Amplifier

Description

The 60V InterFET 2N5463, 2N5464, and 2N5465 are targeted for low noise small signal amplifiers and audio amplifiers. Gate leakages are typically less than 10pA at room temperatures.







Product Summary

	Parameters	2N5463 Min	2N5464 Min	2N5465 Min	Unit
BV_{GSS}	Gate to Source Breakdown Voltage	60	60	60	V
IDSS	Drain to Source Saturation Current	-1	-2	-4	mA
V _{GS(off)}	Gate to Source Cutoff Voltage	0.75	1	1.8	V
G _{FS}	Forward Transconductance	1	1.5	2	mS

Ordering Information Custom Part and Binning Options Available

Part Number	Description	Case	Packaging		
2N5463; 2N5464; 2N5465	Through-Hole	TO-92	Bulk		
SMP5463; SMP5464; SMP5465	Surface Mount	SOT23	Bulk		
SMP5463TR; SMP5464TR; SMP5465TR	7" Tape and Reel: Max 3,000 Pieces 13" Tape and Reel: Max 9,000 Pieces	SOT23	Minimum 1,000 Pieces Tape and Reel		
2N5463COT; 2N5464COT; 2N5465COT	Chip Orientated Tray (COT Waffle Pack)	сот	400/Waffle Pack		
2N5463CFT; 2N5464CFT; 2N5465CFT	Chip Face-up Tray (CFT Waffle Pack)	CFT	400/Waffle Pack		



Disclaimer: It is the Buyers responsibility for designing, validating and testing the end application under all field use cases and extreme use conditions. Guaranteeing the application meets required standards, regulatory compliance, and all safety and security requirements is the responsibility of the Buyer. These resources are subject to change without notice.







Support

Electrical Characteristics

Maximum Ratings (@ T_A = 25°C, Unless otherwise specified)

	Parameters	Value	Unit
VRGS	Reverse Gate Source and Gate Drain Voltage	60	V
I_{FG}	Continuous Forward Gate Current	-10	mA
PD	Continuous Device Power Dissipation	310	mW
Р	Power Derating	2.8	mW/°C
Τı	Operating Junction Temperature	-55 to 125	°C
T _{STG}	Storage Temperature	-65 to 150	°C

Static Characteristics (@ TA = 25°C, Unless otherwise specified)

			2N5463		2N5463 2N5464		2N5465		
	Parameters	Conditions	Min	Max	Min	Max	Min	Max	Unit
V(BR)GSS	Gate to Source Breakdown Voltage	V_{DS} = 0V, I _G = 10 μ A	60		60		60		v
IGSS	Gate to Source Reverse Current	$V_{GS} = 30V, V_{DS} = 0V, T_A = 25^{\circ}C$ $V_{GS} = 30V, V_{DS} = 0V, T_A = 100^{\circ}C$		5 1		5 1		5 1	nA μA
V _{GS(OFF)}	Gate to Source Cutoff Voltage	$V_{DS} = 15V, I_D = 1\mu A$	0.75	6	1	7.5	1.8	9	V
V _{GS}	Gate to Source Voltage	V _{DS} = -15V, I _D = ()	0.5 (-100)	4.0 (-100)	0.8 (-200)	4.5 (-200)	1.5 (-400)	6 (-400)	۷ µA
I _{DSS}	Drain to Source Saturation Current	$V_{DS} = -15V, V_{GS} = 0V$ (Pulsed)	-1	-5	-2	-9	-4	-16	mA

Dynamic Characteristics (@ TA = 25°C, Unless otherwise specified)

			2N5463		2N5464		2N5465		
	Parameters	Conditions	Min	Max	Min	Max	Min	Max	Unit
GFS	Forward Transconductance	V _{DS} = -15V, V _{GS} = 0V, f = 1kHz	1	4	1.5	5	2	6	mS
Gos	Output Conductance	V _{DS} = -15V, V _{GS} = 0V, f = 1kHz		75		75		75	μS
Ciss	Input Capacitance	V_{DS} = -15V, V_{GS} = 0V, f = 1MHz		7		7		7	pF
C _{rss}	Reverse Transfer Capacitance	V_{DS} = -15V, V_{GS} = 0V, f = 1MHz		2		2		2	pF
NF	Noise Figure	V _{DS} = -15V, V _{GS} = 0V, f = 100Hz, BW = 1Hz		2.5		2.5		2.5	dB
en	Equivalent Circuit Input Noise Voltage	$V_{DS} = -15V, V_{GS} = 0V, f = 100Hz, \\ R_G = 1M\Omega$		115		115		115	nV/√Hz



Technical

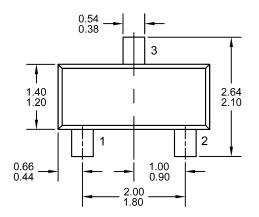
Support

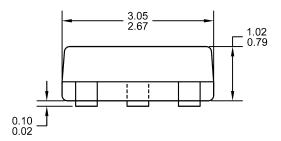
Order

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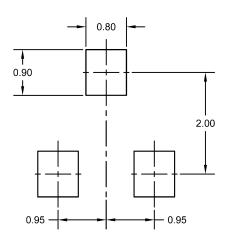
SOT23 (TO-236AB) Mechanical and Layout Data

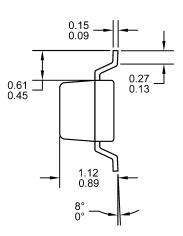
Package Outline Data





Suggested Pad Layout





- 1. All linear dimensions are in millimeters.
- 2. Package weight approximately 0.12 grams
- 3. Molded plastic case UL 94V-0 rated
- For Tape and Reel specifications refer to InterFET CTC-021 Tape and Reel Specification, Document number: IF39002
- 5. Bulk product is shipped in standard ESD shipping material
- 6. Refer to JEDEC standards for additional information.

- 1. All linear dimensions are in millimeters.
- 2. The suggested land pattern dimensions have been provided for reference only. A more robust pattern may be desired for wave soldering.